

**MURF860** 

Technical Data Data Sheet N0344, Rev. A



# MURF860 ULTRAFAST RECTIFIER



#### Features

- Ultra-Fast Switching
- High Current Capability
- Low Reverse Leakage Current
- High Surge Current Capability
- Plastic Material has UL Flammability Classification 94V-O
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

#### **Circuit Diagram**



#### Applications

- Switching Power Supply
- Power Switching Circuits
- General Purpose

#### Maximum Ratings and Electrical Characteristics @T<sub>A</sub>=25°C unless otherwise specified

Characteristic	Symbol	MURF860	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	600	V
RMS Reverse Voltage	V <sub>R(RMS)</sub>	420	V
Average Rectified Output Current @T <sub>A</sub> = 55°C	lo	8.0	A
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	I <sub>FSM</sub>	110	A
Forward Voltage (per element) @l <sub>F</sub> = 8.0A, T <sub>J</sub> =25°C	V <sub>FM1</sub>	2.2	V
@I <sub>F</sub> = 8.0A, T <sub>J</sub> =100°C	V <sub>FM2</sub>	2.0	V
Peak Reverse Current@T <sub>A</sub> = 25°CAt Rated DC Blocking Voltage@T <sub>A</sub> = 100°C	I <sub>RM</sub>	5 50	μA
Maximum Reverse Recovery Time (Note 1)	Trr	50	ns
Max. Voltage Rate of Change	dv/dt	10,000	V/µs
Typical Thermal Resistance Junction to Ambient (Note 2)	R <sub>0JA</sub>	25	K/W
Storage Temperature Range	T <sub>STG,</sub> T <sub>J</sub>	-55 to +150	°C
Approximate Weight	wt	1.6	g

**Note**: 1. Measured with  $I_F$ =0.5A,  $I_R$ =1.0A,  $I_{rr}$ =0.25A

2. Mount on Cu-Pad Size 16mm×16mm on P.C.B.

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#### Technical Data Data Sheet N0344, Rev. A

# Ratings and Characteristics Curves









Fig.3-Typical Forward Voltage Drop Characteristics



RoHS



#### Technical Data Data Sheet N0344, Rev. A



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#### **Mechanical Dimensions ITO-220AC**





SYMBOL	Millimeters		
STNBOL	MIN.	TYP.	MAX.
A	4.30	4.50	4.70
A1	1.10	1.30	1.50
A2	2.80	3.00	3.20
A3	2.50	2.70	2.90
b	0.50	0.60	0.75
b1	1.10	1.20	1.35
b2	1.50	1.60	1.75
С	0.50	0.60	0.75
D	14.80	15.00	15.20
E	9.96	10.16	10.36
е	-	2.55	_
e1	5.00	5.10	5.16
H1	6.50	6.70	6.90
L	12.70	13.20	13.70
L1	1.60	1.80	2.00
L2	0.80	1.00	1.20
L3	0.60	0.80	1.00
L4	-	1.10	1.50
<b>ΦΡ1</b> (上口)	3.30	3.50	3.70
<b>ΦΡ2</b> (下口)	2.99	3.19	3.39
Q	2.50	2.70	2.90
Θ1		5°	
Θ2		4°	
Θ3		10°	
Θ4		5°	
Θ5		5°	

# 

# **Tube Specification**



# **Marking Diagram**

MURF860 SSG XXXXX

Where XXXXX is YYWWL

MUR = I

F

8

60

YY WW

L

SSG

- = Device Type = Package type
- = Forward Current (8A)
  - = Reverse Voltage (600V)
- = SSG
- = Year
- = Week
  - = Lot Number

Cautions: Molding resin Epoxy resin UL:94V-0

# **Ordering Information**

Device	Package	Shipping
MURF860	ITO-220AC (Pb-Free)	50 pcs/ tube

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification

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